



A B S T R A C T

[Abstract of the Disclosure]

A ferroelectric random access memory (FRAM) device and a fabrication method
5 therefor are provided. The FRAM device includes seed layers above and below faces
of electric layer. The upper and lower seed layers are formed for the purpose of
making the characteristics of the upper and lower interfaces of the ferroelectric layer be
the same with each other. Therefore, since the characteristics of the upper and lower
interfaces become the same with each other by the upper and lower seed layers, an
10 imprint phenomenon can be effectively prevented in the ferroelectric random access
memory device.

[Representative Drawing]

FIG. 1